



PLD904-4-T TECHNICAL DATA

Pulsed Infrared Laser Diode

Structure: **MOCVD**
Lasing wavelength: **904 nm**
Peak power: **4 W**
Package: **TO-18T**



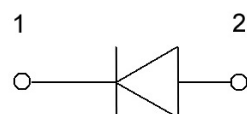
Maximum Ratings (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Peak Output Power	P _o	4	W
Operation Case Temperature	T _c	-30 .. +100	°C
Storage Temperature	T _{STG}	-60 .. +100	°C

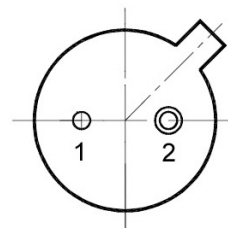
Optical-Electrical Characteristics (Tc = 25°C), Pulselength 50 ns, 1 kHz

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I _{th}	pulsed mode	150	250	350	mA
Peak Current	I _p	P _o = 4 W	-	-	5	A
Peak Voltage	V _p	P _o = 4 W	-	-	6	V
Lasing Wavelength	λ _p	P _o = 4 W	895	904	915	nm
Emitting Aperture	A _E	P _o = 4 W	-	75 x 1	-	μm ²
Beam Divergence	θ _{//}	P _o = 4 W	8	10	11	°
Beam Divergence	θ _⊥	P _o = 4 W	30	40	50	°
Duty Factor	D	P _o = 4 W	-	0.1	-	%

Pin layout:



- 1.) laser diode cathode
- 2.) laser diode anode



Bottom View

* Case and Pin no.1 are common



Drawing:

